

查询"MRF5P21045NR1"供应商



# RF Power Field-Effect Transistor

## N-Channel Enhancement-Mode Lateral MOSFET

Designed for W-CDMA base station applications with frequencies from 2110 to 2170 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. Dual path topology suitable for Doherty, quadrature, single-ended and push-pull applications.

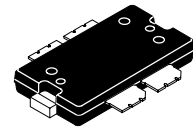
- Typical 2-Carrier W-CDMA Performance:  $V_{DD} = 28$  Volts,  $I_{DQ} = 500$  mA,  $P_{out} = 10$  Watts Avg., Full Frequency Band, Channel Bandwidth = 3.84 MHz, PAR = 8.5 dB @ 0.01% Probability on CCDF.  
 Power Gain — 14.5 dB  
 Drain Efficiency — 25.5%  
 IM3 @ 10 MHz Offset — -37 dBc in 3.84 MHz Channel Bandwidth  
 ACPR @ 5 MHz Offset — -39 dBc in 3.84 MHz Channel Bandwidth
- Capable of Handling 5:1 VSWR, @ 28 Vdc, 2140 MHz, 45 Watts CW Output Power

### Features

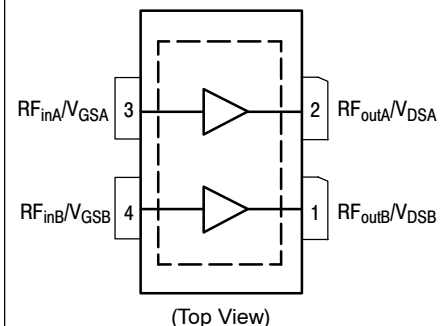
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32  $V_{DD}$  Operation
- Integrated ESD Protection
- 200°C Capable Plastic Package
- RoHS Compliant
- In Tape and Reel. R1 Suffix = 500 Units per 44 mm, 13 inch Reel.

**MRF5P21045NR1**

**2110-2170 MHz, 10 W AVG., 28 V  
 2 x W-CDMA, DUAL PATH  
 LATERAL N-CHANNEL  
 RF POWER MOSFET**



**CASE 1486-03, STYLE 1  
 TO-270 WB-4**



Note: Exposed backside of the package is the source terminal for the transistors.

**Figure 1. Pin Connections**

**Table 1. Maximum Ratings**

| Rating                         | Symbol    | Value        | Unit |
|--------------------------------|-----------|--------------|------|
| Drain-Source Voltage           | $V_{DSS}$ | - 0.5, +65   | Vdc  |
| Gate-Source Voltage            | $V_{GS}$  | - 0.5, +15   | Vdc  |
| Storage Temperature Range      | $T_{stg}$ | - 65 to +150 | °C   |
| Operating Junction Temperature | $T_J$     | 200          | °C   |

**Table 2. Thermal Characteristics**

| Characteristic   | Symbol          | Value (1,2)  | Unit |
|--|-----------------|--------------|------|
| Thermal Resistance, Junction to Case<br>Case Temperature 80°C, 45 W CW<br>Case Temperature 77°C, 10 W CW | $R_{\theta JC}$ | 1.35<br>1.48 | °C/W |

1. MTTF calculator available at <http://www.freescale.com/rf>. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.
2. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

**Table 3. ESD Protection Characteristics**

| Test Methodology                      | Class        |
|---------------------------------------|--------------|
| Human Body Model (per JESD22-A114)    | 1C (Minimum) |
| Machine Model (per EIA/JESD22-A115)   | A (Minimum)  |
| Charge Device Model (per JESD22-C101) | IV (Minimum) |

**Table 4. Moisture Sensitivity Level**

| Test Methodology                      | Rating | Package Peak Temperature | Unit |
|---------------------------------------|--------|--------------------------|------|
| Per JESD 22-A113, IPC/JEDEC J-STD-020 | 3      | 260                      | °C   |

**Table 5. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

| Characteristic  | Symbol    | Min | Typ | Max | Unit            |
|---|-----------|-----|-----|-----|-----------------|
| <b>Off Characteristics</b> <sup>(1)</sup>   |           |     |     |     |                 |
| Zero Gate Voltage Drain Leakage Current<br>( $V_{DS} = 65\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ ) | $I_{DSS}$ | —   | —   | 10  | $\mu\text{Adc}$ |
| Zero Gate Voltage Drain Leakage Current<br>( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ ) | $I_{DSS}$ | —   | —   | 1   | $\mu\text{Adc}$ |
| Gate-Source Leakage Current<br>( $V_{GS} = 5\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )              | $I_{GSS}$ | —   | —   | 1   | $\mu\text{Adc}$ |

**On Characteristics** <sup>(1)</sup>

|  |              |     |     |      |     |
|--|--------------|-----|-----|------|-----|
| Gate Threshold Voltage<br>( $V_{DS} = 10\text{ Vdc}$ , $I_D = 120\ \mu\text{Adc}$ )  | $V_{GS(th)}$ | 2   | —   | 3.5  | Vdc |
| Gate Quiescent Voltage<br>( $V_{DS} = 28\text{ Vdc}$ , $I_D = 500\text{ mAdc}$ )   | $V_{GS(Q)}$  | —   | 3.8 | —    | Vdc |
| Fixture Gate Quiescent Voltage <sup>(2)</sup><br>( $V_{DD} = 28\text{ Vdc}$ , $I_D = 500\text{ mAdc}$ , Measured in Functional Test) | $V_{GG(Q)}$  | 6   | 7.6 | 10   | Vdc |
| Drain-Source On-Voltage<br>( $V_{GS} = 10\text{ Vdc}$ , $I_D = 1.2\text{ Adc}$ )   | $V_{DS(on)}$ | 0.2 | 0.3 | 0.35 | Vdc |

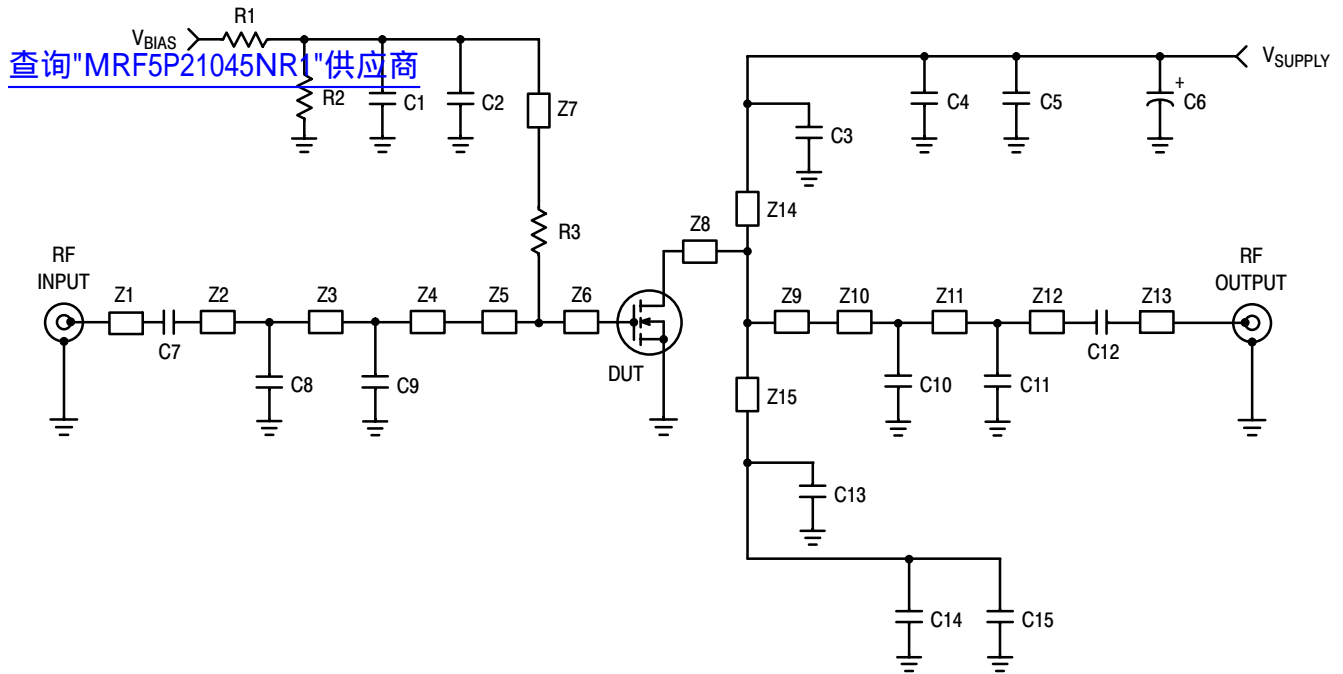
**Dynamic Characteristics** <sup>(1,3)</sup>

|   |           |   |     |   |    |
|---|-----------|---|-----|---|----|
| Reverse Transfer Capacitance<br>( $V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ ) | $C_{rss}$ | — | 0.9 | — | pF |
| Output Capacitance<br>( $V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )           | $C_{oss}$ | — | 124 | — | pF |
| Input Capacitance<br>( $V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )            | $C_{iss}$ | — | 247 | — | pF |

**Functional Tests** <sup>(1)</sup> (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 500\text{ mA}$ ,  $P_{out} = 10\text{ W Avg.}$ ,  $f_1 = 2112.5\text{ MHz}$ ,  $f_2 = 2122.5\text{ MHz}$  and  $f_1 = 2157.5\text{ MHz}$ ,  $f_2 = 2167.5\text{ MHz}$ , 2-Carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers. ACPR measured in 3.84 MHz Channel Bandwidth @  $\pm 5\text{ MHz}$  Offset. IM3 measured in 3.84 MHz Bandwidth @  $\pm 10\text{ MHz}$  Offset. PAR = 8.5 dB @ 0.01% Probability on CCDF.

|                              |          |      |      |      |     |
|------------------------------|----------|------|------|------|-----|
| Power Gain                   | $G_{ps}$ | 13.5 | 14.5 | 16.5 | dB  |
| Drain Efficiency             | $\eta_D$ | 23.5 | 25.5 | —    | %   |
| Intermodulation Distortion   | IM3      | —    | -37  | -35  | dBc |
| Adjacent Channel Power Ratio | ACPR     | —    | -39  | -37  | dBc |
| Input Return Loss            | IRL      | —    | -12  | -8   | dB  |

1. Measurement made with device in single-ended configuration. (See Figure 4, Possible Circuit Topologies)
2.  $V_{GG} = 2 \times V_{GS(Q)}$ . Parameter measured on Freescale Test Fixture, due to resistive divider network on the board. Refer to Test Circuit schematic.
3. Part internally matched both on input and output.



|         |                            |          |  |
|---------|----------------------------|----------|--|
| Z1, Z13 | 0.250" x 0.080" Microstrip | Z9       | 0.385" x 1.000" Microstrip                     |
| Z2      | 1.012" x 0.080" Microstrip | Z10      | 0.179" x 0.080" Microstrip                     |
| Z3      | 0.165" x 0.080" Microstrip | Z11      | 0.527" x 0.080" Microstrip                     |
| Z4      | 0.378" x 0.080" Microstrip | Z12      | 0.789" x 0.080" Microstrip                     |
| Z5      | 0.365" x 1.000" Microstrip | Z14, Z15 | 0.270" x 0.080" Microstrip                     |
| Z6, Z8  | 0.115" x 1.000" Microstrip | PCB      | Taconic TLX8-0300, 0.030", $\epsilon_r = 2.55$ |
| Z7      | 0.510" x 0.080" Microstrip |          |  |

Figure 2. MRF5P21045NR1 Test Circuit Schematic — Single-Ended Configuration

Table 6. MRF5P21045NR1 Test Circuit Component Designations and Values — Single-Ended Configuration

| Part                 | Description                                      | Part Number        | Manufacturer     |
|----------------------|--|--------------------|------------------|
| C1                   | 220 nF Chip Capacitor                            | 18125C224KAT4A     | AVX              |
| C2, C3, C7, C12, C13 | 6.8 pF Chip Capacitors                           | ATC100B6R8BT500XT  | ATC              |
| C4, C5, C14, C15     | 6.8 $\mu$ F Chip Capacitors                      | C4532X5R1H685MT    | TDK              |
| C6                   | 220 $\mu$ F, 63 V Electrolytic Capacitor, Radial | EMVY630ATR221MKE0S | Nippon Chemi-Con |
| C8, C10              | 1 pF Chip Capacitors                             | ATC100B1R0BT500XT  | ATC              |
| C9                   | 1.5 pF Chip Capacitor                            | ATC100B1R5BT500XT  | ATC              |
| C11                  | 0.5 pF Chip Capacitor                            | ATC100B0R5BT500XT  | ATC              |
| R1, R2               | 10 k $\Omega$ , 1/4 W Chip Resistors             | CRCW12061001FKTA   | Vishay           |
| R3                   | 10 $\Omega$ , 1/4 W Chip Resistor                | CRCW120610R0FKTA   | Vishay           |

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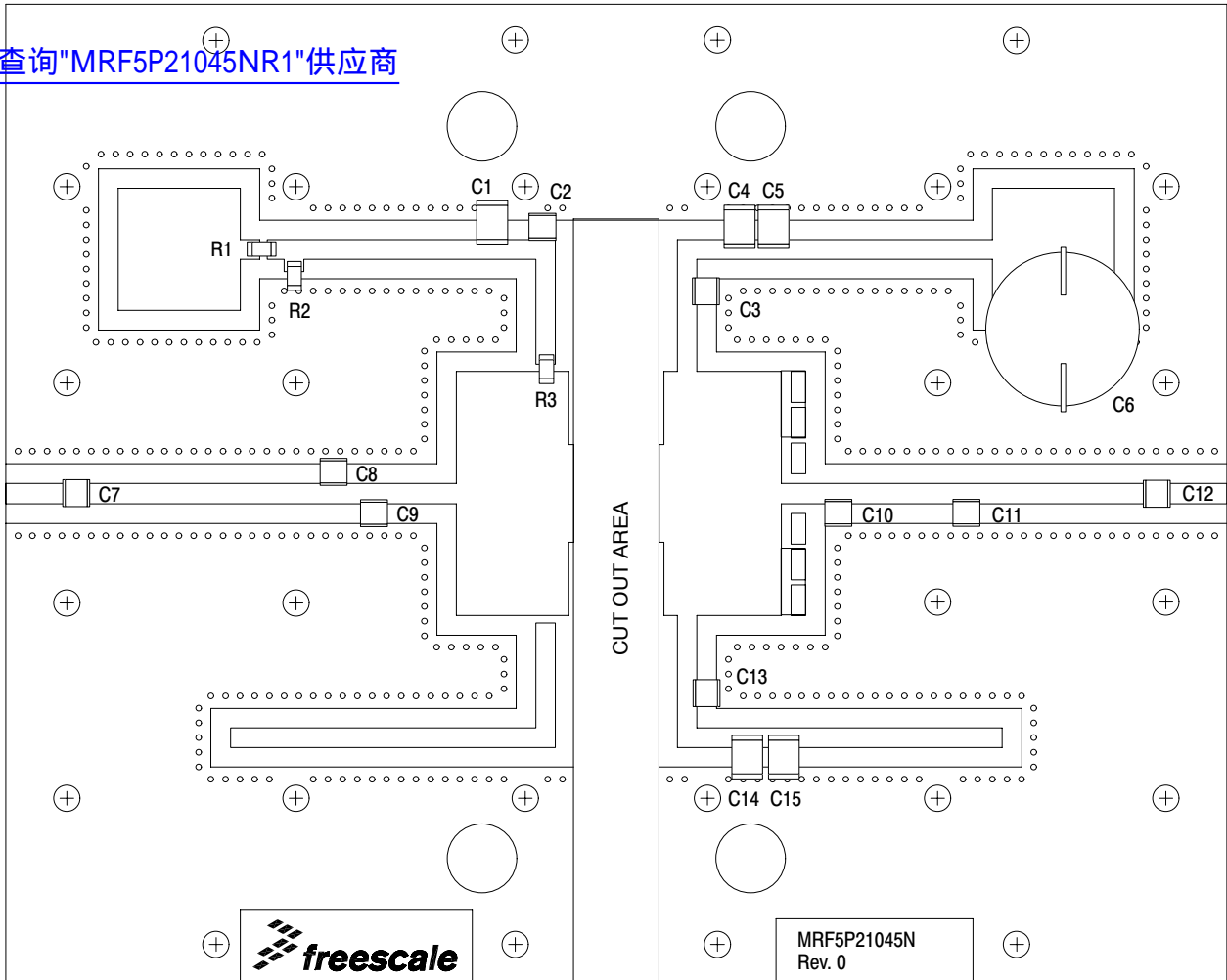


Figure 3. MRF5P21045NR1 Test Circuit Component Layout — Single-Ended Configuration

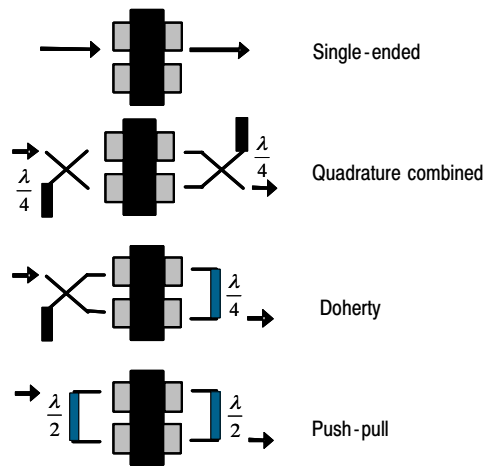
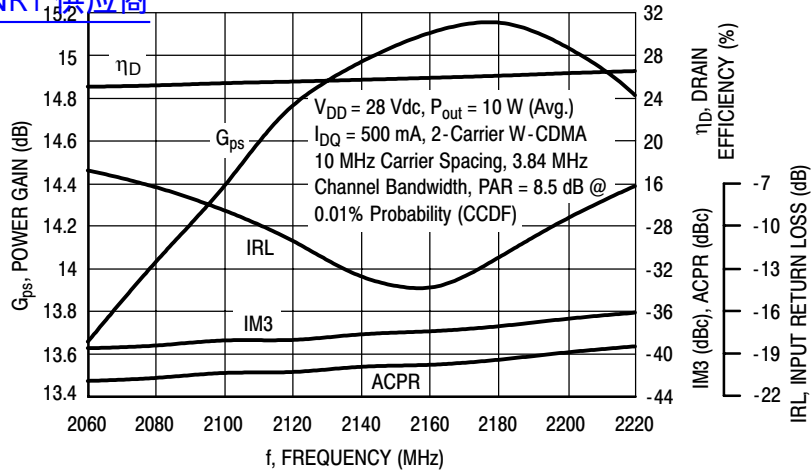


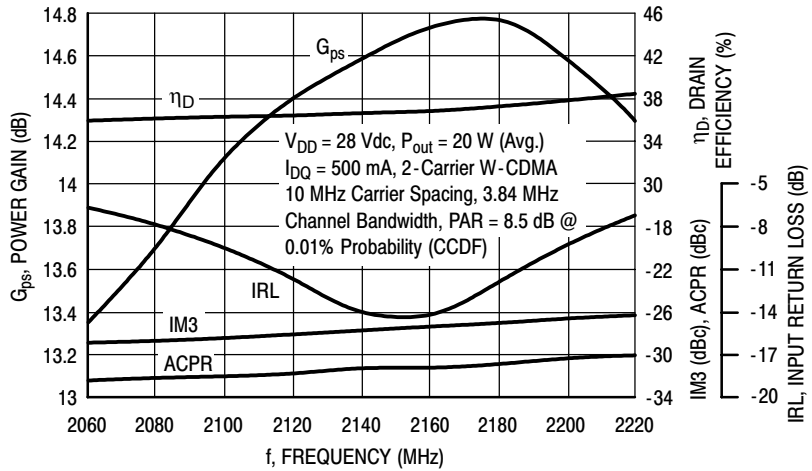
Figure 4. Possible Circuit Topologies

## TYPICAL CHARACTERISTICS

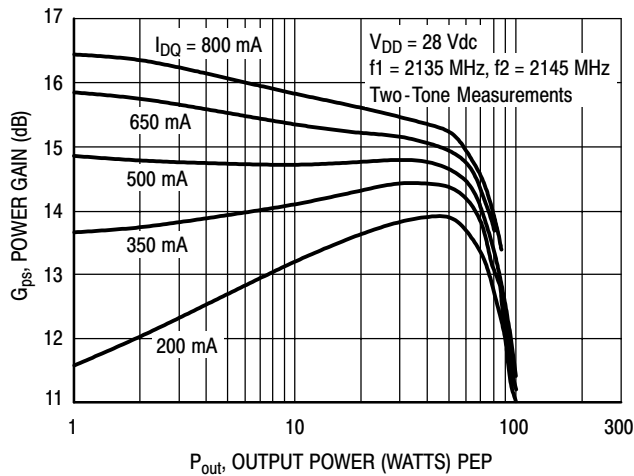
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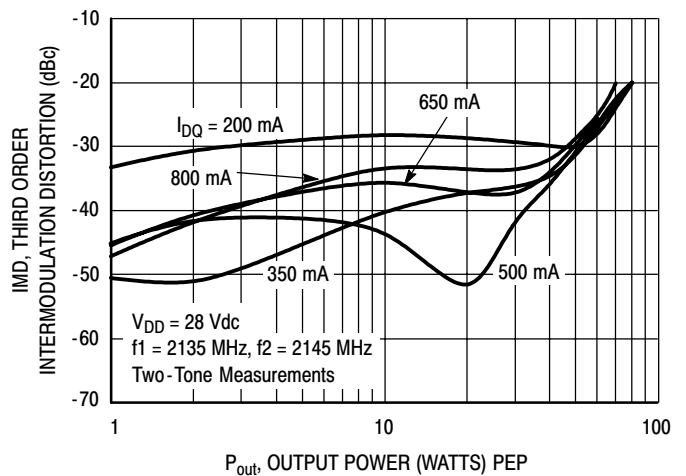
**Figure 5. 2-Carrier W-CDMA Broadband Performance @  $P_{out} = 10$  Watts Avg.**



**Figure 6. 2-Carrier W-CDMA Broadband Performance @  $P_{out} = 20$  Watts Avg.**



**Figure 7. Two-Tone Power Gain versus Output Power**



**Figure 8. Third Order Intermodulation Distortion versus Output Power**

## TYPICAL CHARACTERISTICS

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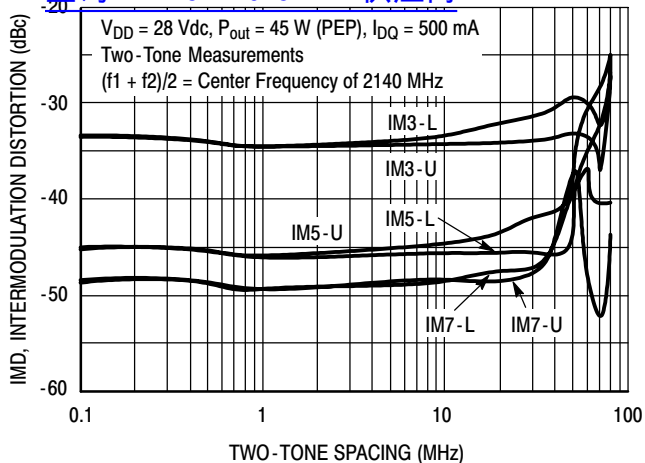


Figure 9. Intermodulation Distortion Products versus Tone Spacing

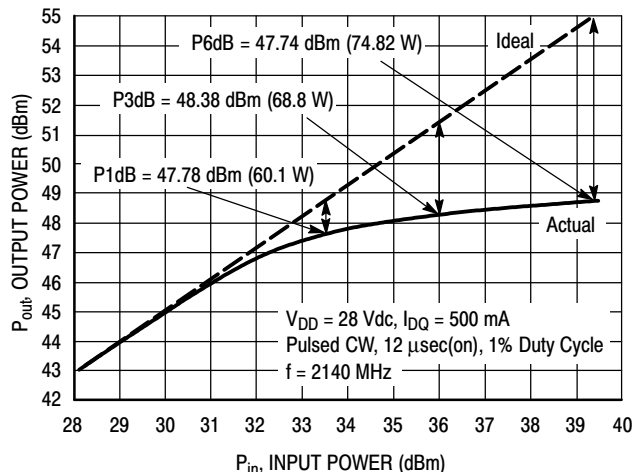


Figure 10. Pulsed CW Output Power versus Input Power

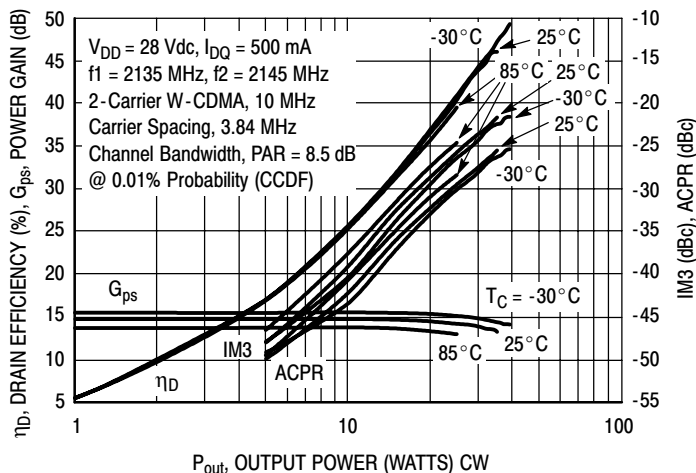


Figure 11. 2-Carrier W-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power

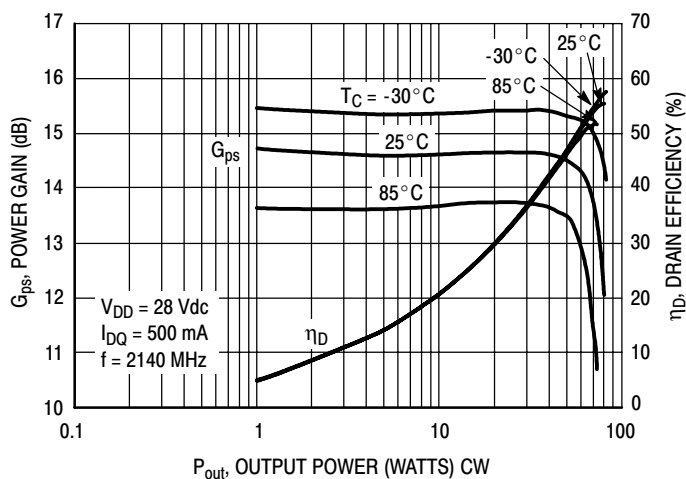


Figure 12. Power Gain and Drain Efficiency versus CW Output Power

## TYPICAL CHARACTERISTICS

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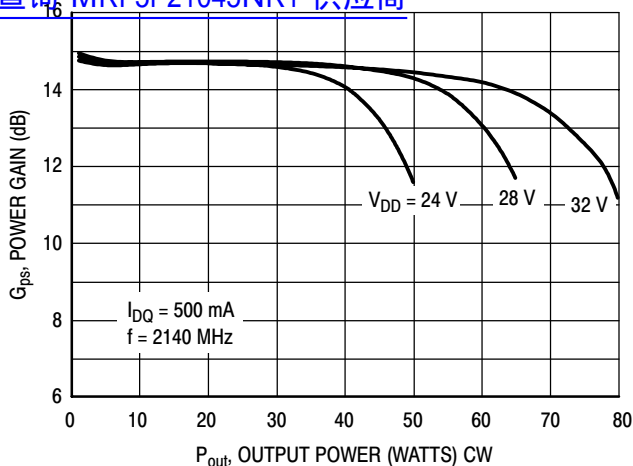
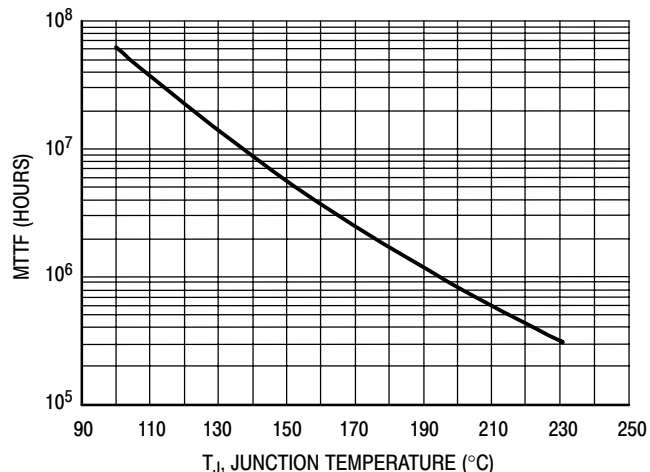


Figure 13. Power Gain versus Output Power



This above graph displays calculated MTTF in hours when the device is operated at  $V_{DD} = 28 \text{ Vdc}$ ,  $P_{out} = 10 \text{ W Avg.}$ , and  $\eta_D = 25.5\%$ .

MTTF calculator available at <http://www.freescale.com/rf>. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.

Figure 14. MTTF versus Junction Temperature

## W-CDMA TEST SIGNAL

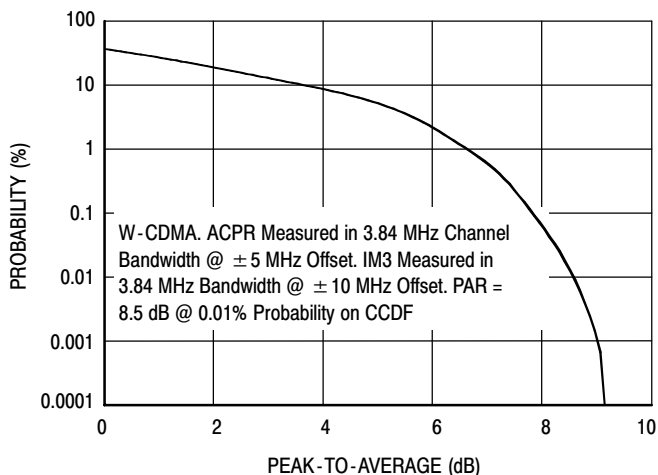


Figure 15. CCDF W-CDMA 3GPP, Test Model 1, 64 DPCH, 67% Clipping, Single-Carrier Test Signal

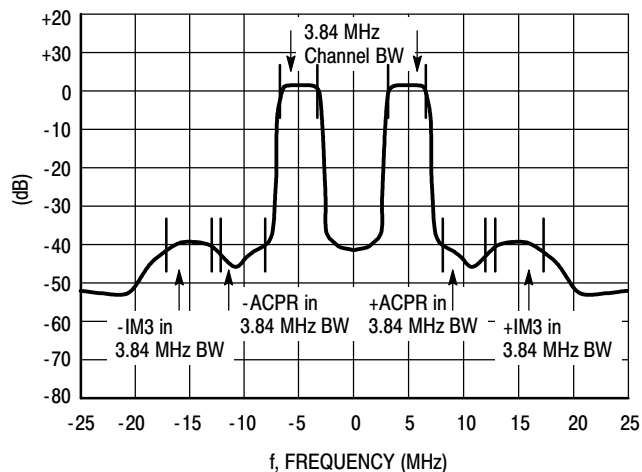
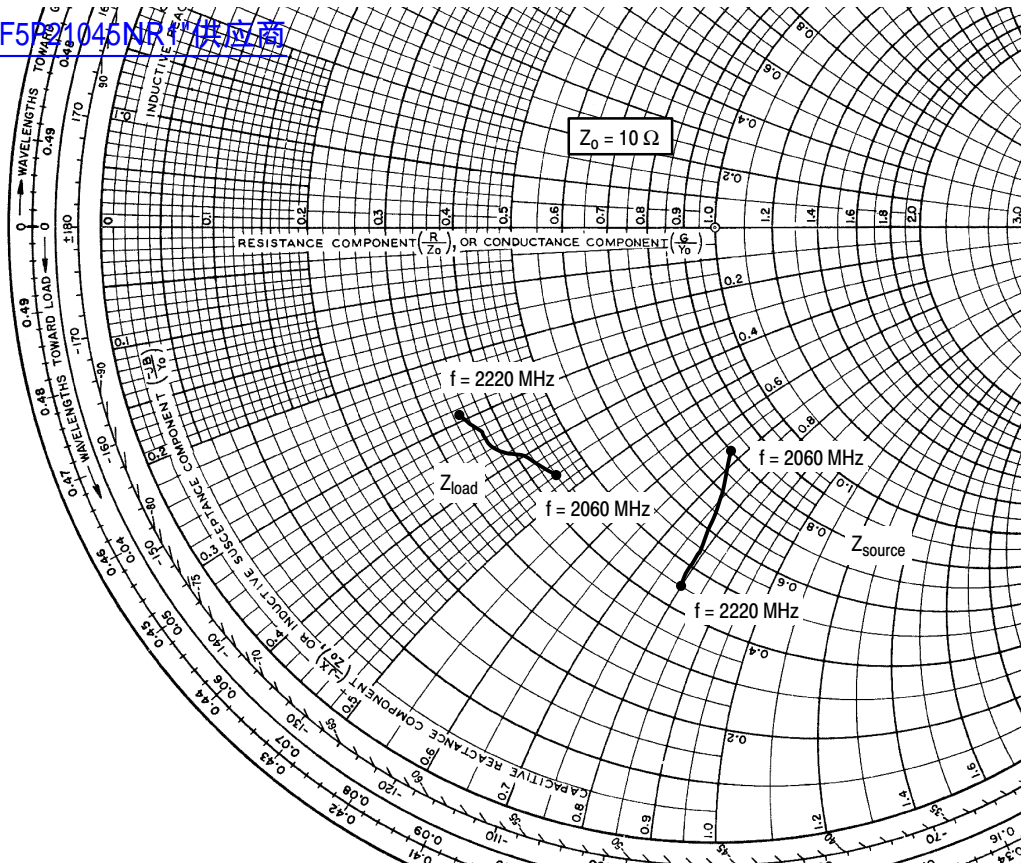


Figure 16. 2-Carrier W-CDMA Spectrum



$V_{DD} = 28 \text{ Vdc}$ ,  $I_{DQ} = 500 \text{ mA}$ ,  $P_{out} = 10 \text{ W Avg.}$

| f<br>MHz | $Z_{source}$<br>$\Omega$ | $Z_{load}$<br>$\Omega$ |
|----------|--------------------------|------------------------|
| 2060     | 8.01 - j6.68             | 4.38 - j4.62           |
| 2080     | 7.66 - j6.94             | 4.27 - j4.43           |
| 2100     | 7.26 - j7.20             | 4.12 - j4.04           |
| 2120     | 6.76 - j7.45             | 3.98 - j3.90           |
| 2140     | 6.28 - j7.71             | 3.81 - j3.69           |
| 2160     | 5.82 - j7.78             | 3.73 - j3.50           |
| 2180     | 5.37 - j7.85             | 3.65 - j3.30           |
| 2200     | 4.92 - j7.85             | 3.57 - j3.11           |
| 2220     | 4.46 - j7.97             | 3.49 - j2.92           |

$Z_{source}$  = Test circuit impedance as measured from gate to ground.

$Z_{load}$  = Test circuit impedance as measured from drain to ground.

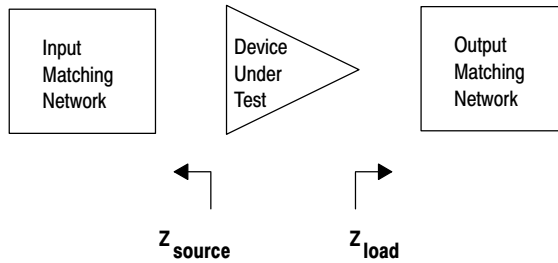
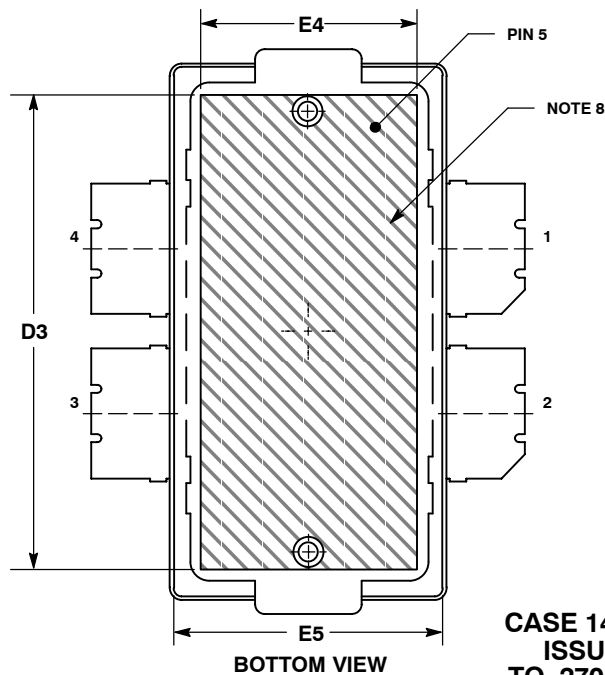
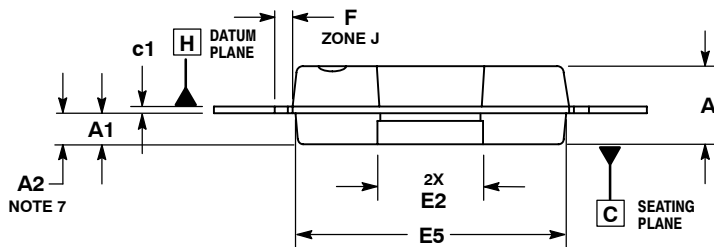
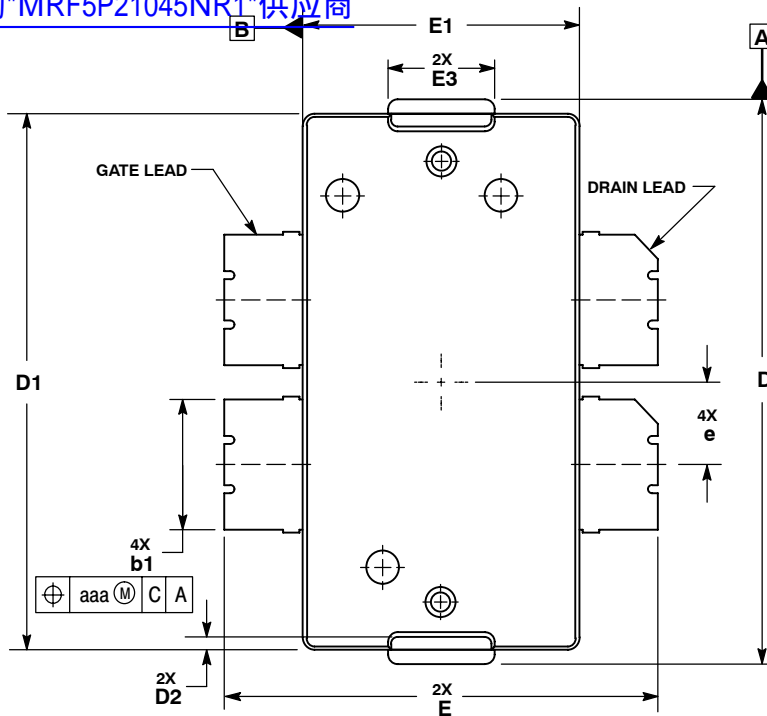


Figure 17. Series Equivalent Source and Load Impedance — Single-Ended Configuration



# PACKAGE DIMENSIONS

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**CASE 1486-03  
ISSUE C  
TO-270 WB-4  
PLASTIC**

**NOTES:**

1. CONTROLLING DIMENSION: INCH.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DATUM PLANE -H- IS LOCATED AT THE TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
5. DIMENSION "b1" DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 TOTAL IN EXCESS OF THE "b1" DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. DATUMS -A- AND -B- TO BE DETERMINED AT DATUM PLANE -H-.
7. DIMENSION A2 APPLIES WITHIN ZONE "J" ONLY.
8. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG.

| DIM | INCHES   |      | MILLIMETERS |       |
|-----|----------|------|-------------|-------|
|     | MIN      | MAX  | MIN         | MAX   |
| A   | .100     | .104 | 2.54        | 2.64  |
| A1  | .039     | .043 | 0.99        | 1.09  |
| A2  | .040     | .042 | 1.02        | 1.07  |
| D   | .712     | .720 | 18.08       | 18.29 |
| D1  | .688     | .692 | 17.48       | 17.58 |
| D2  | .011     | .019 | 0.28        | 0.48  |
| D3  | .600     | ---  | 15.24       | ---   |
| E   | .551     | .559 | 14          | 14.2  |
| E1  | .353     | .357 | 8.97        | 9.07  |
| E2  | .132     | .140 | 3.35        | 3.56  |
| E3  | .124     | .132 | 3.15        | 3.35  |
| E4  | .270     | ---  | 6.86        | ---   |
| E5  | .346     | .350 | 8.79        | 8.89  |
| F   | .025 BSC |      | 0.64 BSC    |       |
| b1  | .164     | .170 | 4.17        | 4.32  |
| c1  | .007     | .011 | 0.18        | 0.28  |
| e   | .106 BSC |      | 2.69 BSC    |       |
| aaa | .004     |      | 0.10        |       |

**STYLE 1:**

- PIN 1. DRAIN
- DRAIN
- GATE
- GATE
- SOURCE

## PRODUCT DOCUMENTATION

[查询"MRF5P21045NR1"供应商](#)  
Refer to the following documents to aid your design process.

### Application Notes

- AN1907: Solder Reflow Attach Method for High Power RF Devices in Plastic Packages
- AN1955: Thermal Measurement Methodology of RF Power Amplifiers
- AN3263: Bolt Down Mounting Method for High Power RF Transistors and RFICs in Over-Molded Plastic Packages

### Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

## REVISION HISTORY

The following table summarizes revisions to this document.

| Revision | Date       | Description   |
|----------|------------|---|
| 0        | April 2007 | <ul style="list-style-type: none"><li>• Initial Release of Data Sheet</li></ul> |

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